

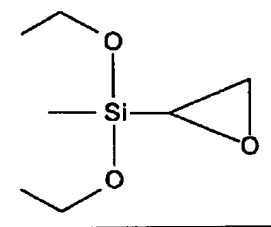
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Section II. (Amendment to the Claims)

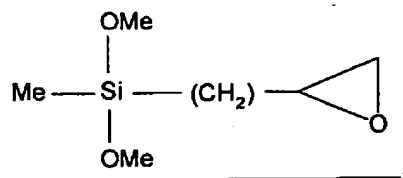
Please amend claims 1, 11, 12, 19, 22, 40, 50 and 51, withdraw claims 18-21, and cancel claims 2, 4-10, 13, 30, 32-34, 41, 43-49 and 52, as set out below in the listing of claims 1-66 of the application.

1. (Currently Amended) An organosilicon precursor for vapor deposition of a low k, high strength dielectric film, wherein the precursor comprises at least one silicon-pendant oxiranyl functionality and is selected from the group consisting of compounds of Formula (A) and Formula (B):

Formula (A), $\text{Me}(\text{EtO})_2\text{SiCHCH}_2\text{O}$:



Formula (B), $\text{Me}(\text{MeO})_2\text{SiCH}_2\text{CHCH}_2\text{O}$:



2.-10. (Cancelled)

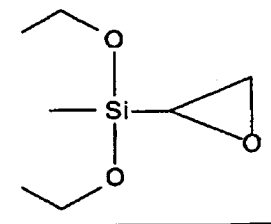
11. (Currently Amended) The organosilicon precursor of claim 1 +0, having Formula (A).

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12. (Currently Amended) The organosilicon precursor of claim 1, having Formula (B).
- 13.-17. (Cancelled)
18. (Withdrawn) The organosilicon precursor of claim 1, wherein the precursor further comprises TMCTS.
19. (Withdrawn) An organosilicon precursor composition for vapor deposition of a low k, high strength dielectric film, wherein the composition comprises:

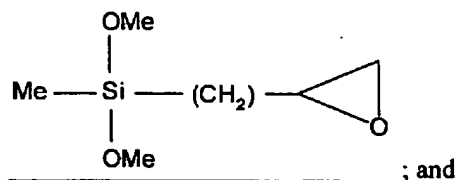
(A) an organosilicon precursor comprising at least one silicon-pendant oxiranyl functionality, wherein said organosilicon precursor is selected from the group consisting of compounds of Formula (A) and Formula (B):

Formula (A), $\text{Me}(\text{EtO})_2\text{SiCHCH}_2\text{O}$:



Formula (B), $\text{Me}(\text{MeO})_2\text{SiCH}_2\text{CHCH}_2\text{O}$:

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(B) a porogen.

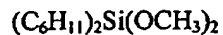
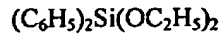
20. (Withdrawn) The organosilicon precursor composition of claim 19, wherein said porogen is selected from the group consisting of compounds of the formula (X):



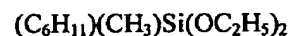
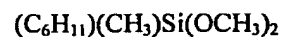
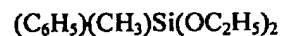
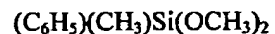
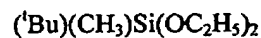
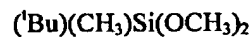
wherein:

each of R^{10} , R^{11} , R^{12} and R^{13} can be the same as or different from one another and each is independently selected from the group consisting of H, C_1 - C_8 alkyl, C_1 - C_8 alkoxy, C_6 - C_{10} cycloalkyl, and C_6 - C_{10} aryl, with the proviso that at least one of R^{10} , R^{11} , R^{12} and R^{13} is C_1 - C_8 alkoxy.

21. (Withdrawn) The organosilicon precursor composition of claim 19, wherein said porogen is selected from the group consisting of:

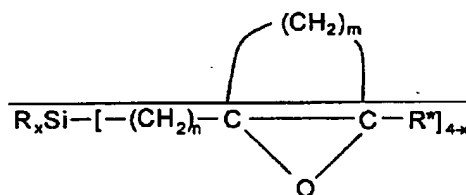


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wherein ${}^t\text{Bu}$ is tertiary butyl.

22. (Withdrawn) A method of forming an oxiranylsilane compound of formula (I):



(I)

wherein:

m is an integer having a value of 0 to 6, inclusive;

n is 0 or 1;

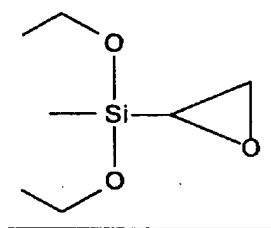
x is an integer having a value of 0 to 3, inclusive; and

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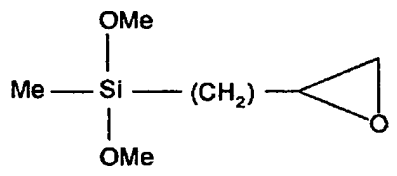
~~each R and R^a can be the same as or different from one another and each is independently selected from the group consisting of H, C₁-C₈ alkyl, C₁-C₈ fluoroalkyl, C₁-C₈ alkoxy, C₆-C₁₀ cycloalkyl, C₆-C₁₀ aryl, C₆-C₁₀ fluoroaryl, C₂-C₆ vinyl, and C₂-C₆ allyl;~~

selected from the group consisting of compounds of Formula (A) and Formula (B):

Formula (A), Me(EtO)₂SiCHCH₂O :



Formula (B), Me(MeO)₂Si CH₂CHCH₂O :



said method comprising oxidizing a corresponding vinylsilane or allylsilane compound.

23. (Withdrawn) The method of claim 22, wherein the step of oxidizing comprises reaction with an oxidizing agent that is inert in relation to Si-OR fragments.

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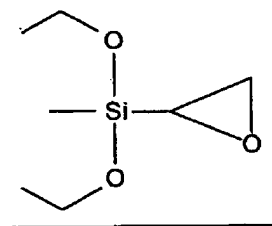
24. (Withdrawn) The method of claim 23, wherein said oxidizing agent comprises an agent selected from the group consisting of meta-Cl(C₆H₄)C(O)OOH, 'BuOOH, wherein 'Bu is tertiary butyl, and Me₃OOSiMe₃, wherein Me is methyl.
25. (Withdrawn) The method of claim 23, wherein said oxidizing agent comprises meta-Cl(C₆H₄)C(O)OOH.
26. (Withdrawn) The method of claim 22, wherein said step of oxidizing is conducted in a non-flammable solvent medium.
27. (Withdrawn) The method of claim 26, wherein said non-flammable solvent medium comprises dichloromethane.
28. (Withdrawn) The method of claim 26, wherein said non-flammable solvent medium comprises chloroform.
29. (Withdrawn) The method of claim 22, wherein said oxiranylsilane compound is Me(EtO)₂SiCHCH₂O.
30. (Cancelled)
31. (Withdrawn) The method of claim 22, wherein said oxiranylsilane is Me(MeO)₂SiCH₂CHCH₂O.

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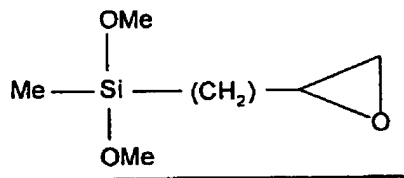
32.-39. (Cancelled)

40. (Withdrawn) A method of forming a low k, high strength dielectric film on a substrate, comprising vapor depositing said film on the substrate from an organosilicon precursor, wherein said precursor comprises comprising at least one silicon-pendant oxiranyl functionality and is selected from the group consisting of compounds of Formula (A) and Formula (B):

Formula (A), $\text{Me}(\text{EtO})_2\text{SiCHCH}_2\text{O}$:



Formula (B), $\text{Me}(\text{MeO})_2\text{SiCH}_2\text{CHCH}_2\text{O}$:



41.-49 (Cancelled)

50. (Withdrawn) The method of claim 40 49, wherein the precursor comprises a compound of Formula (A).

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51. (Withdrawn) The method of claim 40 49, wherein the precursor comprises a compound of Formula (B).

52-56. (Cancelled)

57. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises use of a porogen in combination with said precursor.

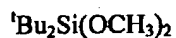
58. (Withdrawn) The method of claim 57, wherein said porogen is selected from the group consisting of compounds of the formula (X):



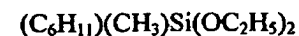
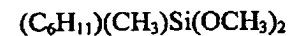
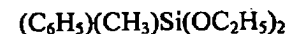
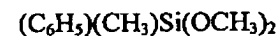
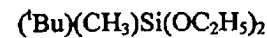
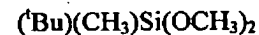
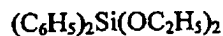
wherein:

each of R^{10} , R^{11} , R^{12} and R^{13} can be the same as or different from one another and each is independently selected from the group consisting of H, $\text{C}_1\text{-C}_8$ alkyl, $\text{C}_1\text{-C}_8$ alkoxy, $\text{C}_6\text{-C}_{10}$ cycloalkyl, and $\text{C}_6\text{-C}_{10}$ aryl, with the proviso that at least one of R^{10} , R^{11} , R^{12} and R^{13} is $\text{C}_1\text{-C}_8$ alkoxy.

59. (Withdrawn) The method of claim 57, wherein said porogen is selected from the group consisting of:



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wherein ^tBu is tertiary butyl.

60. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises chemical vapor deposition.

61. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises plasma-enhanced chemical vapor deposition.

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62. (Withdrawn) The method of claim 40, wherein said vapor depositing step comprises flowing said precursor to a vapor deposition locus in a carrier gas.

63. (Withdrawn) The method of claim 62, wherein said carrier gas comprises carbon dioxide.

64. (Withdrawn) The method of claim 62, wherein the precursor and the carrier gas are the only potential sources of oxygen at the vapor deposition locus.

65. (Withdrawn) The method of claim 40, wherein the precursor is selected from the group consisting of:

$\text{Me}(\text{EtO})_2\text{SiCHCH}_2\text{O}$;

$\text{Me}(\text{MeO})_2\text{SiCH}_2\text{CHCH}_2\text{O}$; and

$\text{Me}_2\text{Si}(\text{CHCH}_2\text{O})_2$.

66. (Withdrawn) The method of claim 40, wherein the precursor further comprises TMCTS.

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